

High Speed CMOS Logic Hex Buffer/Line Driver, Three-State Non-Inverting and Inverting

November 1997 - Revised October 2003

Features

- **Buffered Inputs**
- **High Current Bus Driver Outputs**
- **Typical Propagation Delay t_{PLH} , t_{PHL} = 8ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C**
- **Fanout (Over Temperature Range)**
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- **Wide Operating Temperature Range . . . -55°C to 125°C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
 - 2V to 6V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V
- **HCT Types**
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, V_{IL} = 0.8V (Max), V_{IH} = 2V (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

low power Schottky TTL circuits. Both circuits are capable of driving up to 15 low power Schottky inputs.

The 'HC365 and 'HCT365 are non-inverting buffers, whereas the 'HC366 is an inverting buffer. These devices have two three-state control inputs ($\overline{OE1}$ and $\overline{OE2}$) which are NORed together to control all six gates.

The 'HCT365 logic families are speed, function and pin compatible with the standard LS logic family.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC365F3A	-55 to 125	16 Ld CERDIP
CD54HC366F3A	-55 to 125	16 Ld CERDIP
CD54HCT365F3A	-55 to 125	16 Ld CERDIP
CD74HC365E	-55 to 125	16 Ld PDIP
CD74HC365M	-55 to 125	16 Ld SOIC
CD74HC365MT	-55 to 125	16 Ld SOIC
CD74HC365M96	-55 to 125	16 Ld SOIC
CD74HC366E	-55 to 125	16 Ld PDIP
CD74HC366M	-55 to 125	16 Ld SOIC
CD74HC366M96	-55 to 125	16 Ld SOIC
CD74HCT365E	-55 to 125	16 Ld PDIP
CD74HCT365M	-55 to 125	16 Ld SOIC
CD74HCT365MT	-55 to 125	16 Ld SOIC
CD74HCT365M96	-55 to 125	16 Ld SOIC

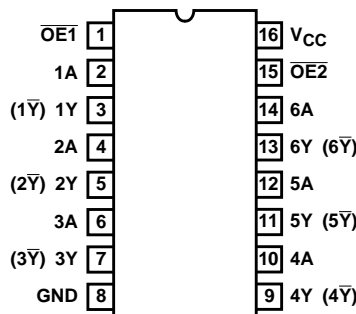
NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and reel. The suffix T denotes a small-quantity reel of 250.

Description

The 'HC365, 'HCT365, and 'HC366 silicon gate CMOS three-state buffers are general purpose high-speed non-inverting and inverting buffers. They have high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to

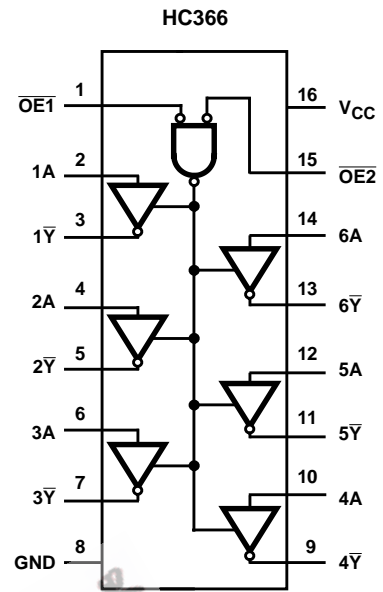
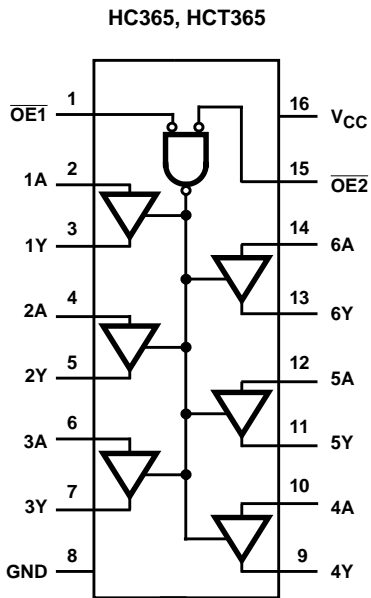
Pinout

CD54HC365, CD54HCT365, CD54HC366
(CERDIP)
CD74HC365, CD74HCT365, CD74HC366
(PDIP, SOIC)
TOP VIEW



CD54/74HC365, CD54/74HCT365, CD54/74HC366

Functional Diagrams



TRUTH TABLE

INPUTS			OUTPUTS (Y)	
OE1	OE2	A	HC/HCT365	HC366
L	L	L	L	H
L	L	H	H	L
X	H	X	Z	Z
H	X	X	Z	Z

NOTE:

H = High Voltage Level

L = Low Voltage Level

X = Don't Care

Z = High Impedance (OFF) State

CD54/74HC365, CD54/74HCT365, CD54/74HC366

Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Drain Current, per Output, I_O	
For $-0.5V < V_O < V_{CC} + 0.5V$	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC}	$\pm 50mA$

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} ($^{\circ}C/W$)
E (PDIP) Package	67
M (SOIC) Package	73
Maximum Junction Temperature	$150^{\circ}C$
Maximum Storage Temperature Range	$-65^{\circ}C$ to $150^{\circ}C$
Maximum Lead Temperature (Soldering 10s)	$300^{\circ}C$ (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range, T_A	$-55^{\circ}C$ to $125^{\circ}C$
Supply Voltage Range, V_{CC}	
HC Types	2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- The package thermal impedance is calculated in accordance with JEDEC 51-7.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS			25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS	
		V_I (V)	I_O (mA)	V_{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX		
HC TYPES													
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V	
				4.5	3.15	-	-	3.15	-	3.15	-	V	
				6	4.2	-	-	4.2	-	4.2	-	V	
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V	
				4.5	-	-	1.35	-	1.35	-	1.35	V	
				6	-	-	1.8	-	1.8	-	1.8	V	
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	V_{OH}	V_{IH} or V_{IL}	-6	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
-7.8			-7.8	6	5.48	-	-	5.34	-	5.2	-	V	
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{IH} or V_{IL}	6	6	4.5	-	-	0.26	-	0.33	-	0.4	V
7.8			7.8	6	-	-	0.26	-	0.33	-	0.4	V	
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	± 0.1	-	± 1	-	± 1	μA	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	μA	

CD54/74HC365, CD54/74HCT365, CD54/74HC366

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 2)	ΔI _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	5.5	-	-	±0.5	-	±5.0	-	±10	μA

NOTE:

2. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
OE ₁	0.6
All Others	0.55

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

Switching Specifications - HC/HCT365 Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay, Data to Outputs HC/HCT365	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	105	130	160	ns
			4.5	-	21	26	32	ns
			6	-	18	22	27	ns
		C _L = 15pF	5	8	-	-	-	ns

CD54/74HC365, CD54/74HCT365, CD54/74HC366

Switching Specifications - HC/HCT365 Input $t_r, t_f = 6\text{ns}$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
Propagation Delay, Data to Outputs HC366	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	110	140	165	ns
			4.5	-	22	28	33	ns
			6	-	19	24	28	ns
		$C_L = 15\text{pF}$	5	9	-	-	-	ns
Propagation Delay, Output Enable and Disable to Outputs	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	40	-	-	-	pF
HCT TYPES								
Propagation Delay, Data to Outputs HC/HCT365	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	9	-	-	-	ns
Propagation Delay, Data to Outputs HC366	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	27	34	41	ns
		$C_L = 15\text{pF}$	5	11	-	-	-	ns
Propagation Delay, Output Enable and Disable to Outputs	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	35	44	53	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	4.5	-	12	15	18	ns
Input Capacitance	C_{IN}	-	-	-	10	10	10	pF
Three-State Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	42	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per buffer.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

CD54/74HC365, CD54/74HCT365, CD54/74HC366

Test Circuits and Waveforms

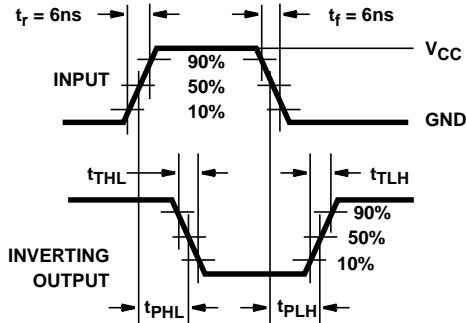


FIGURE 2. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

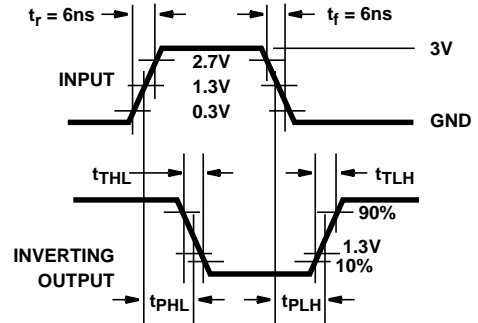


FIGURE 3. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

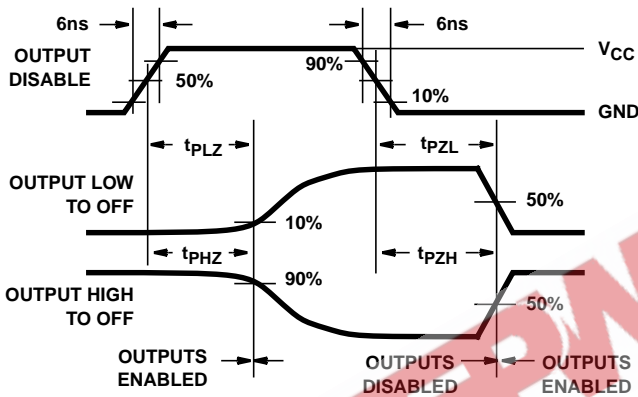


FIGURE 4. HC THREE-STATE PROPAGATION DELAY WAVEFORM

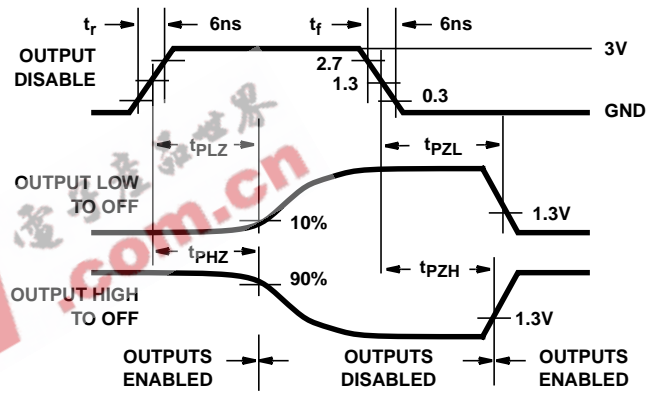
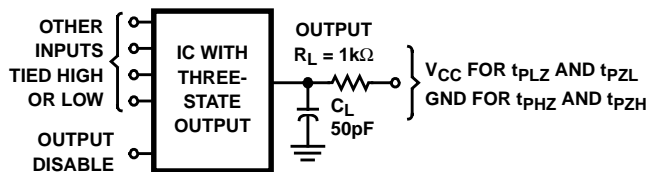


FIGURE 5. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 6. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
CD54HC365F3A	ACTIVE	CDIP	J	16	1	TBD	Call TI	Level-NC-NC-NC
CD54HC366F3A	ACTIVE	CDIP	J	16	1	TBD	Call TI	Level-NC-NC-NC
CD54HCT365F3A	ACTIVE	CDIP	J	16	1	TBD	Call TI	Level-NC-NC-NC
CD74HC365E	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
CD74HC365M	ACTIVE	SOIC	D	16	40	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
CD74HC365M96	ACTIVE	SOIC	D	16	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
CD74HC365MT	ACTIVE	SOIC	D	16	250	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
CD74HC366E	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
CD74HC366M	ACTIVE	SOIC	D	16	40	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
CD74HC366M96	ACTIVE	SOIC	D	16	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
CD74HCT365E	ACTIVE	PDIP	N	16	25	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
CD74HCT365M	ACTIVE	SOIC	D	16	40	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
CD74HCT365M96	ACTIVE	SOIC	D	16	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
CD74HCT365MT	ACTIVE	SOIC	D	16	250	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

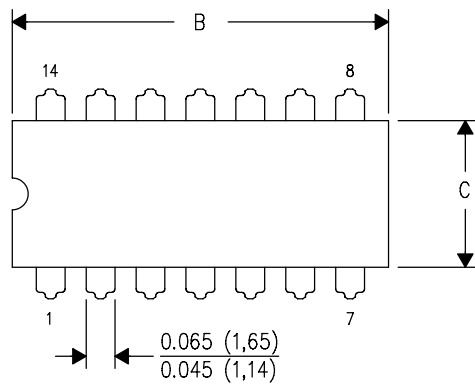
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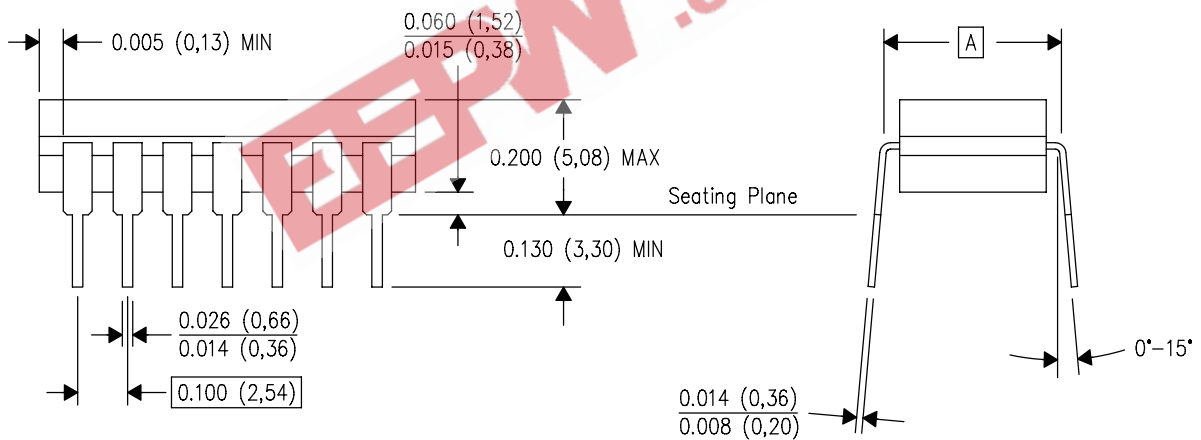
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J (R-GDIP-T**)
14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



DIM \ PINS **	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)



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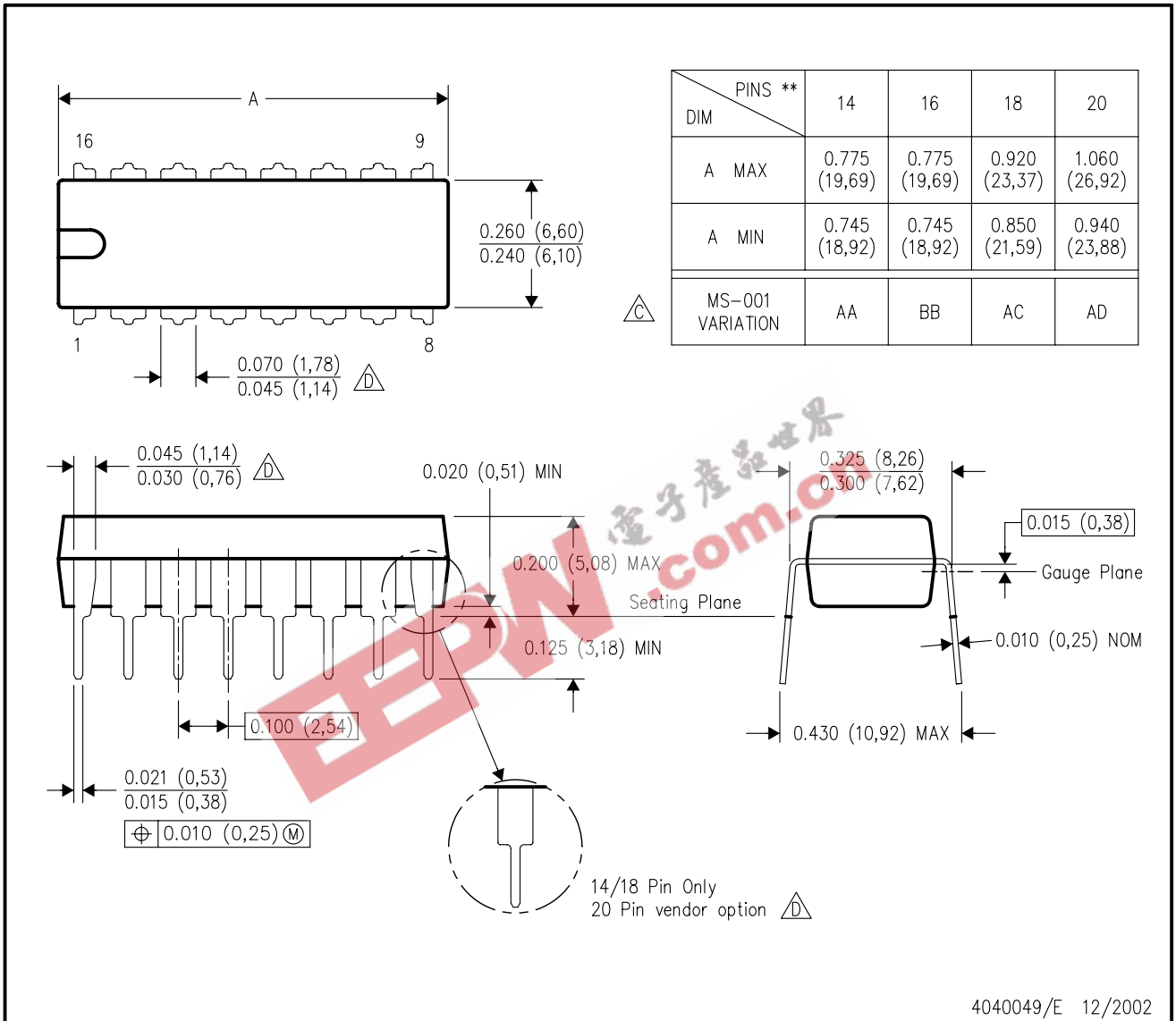
- NOTES:
- All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice.
 - This package is hermetically sealed with a ceramic lid using glass frit.
 - Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
 - Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

MECHANICAL DATA

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN

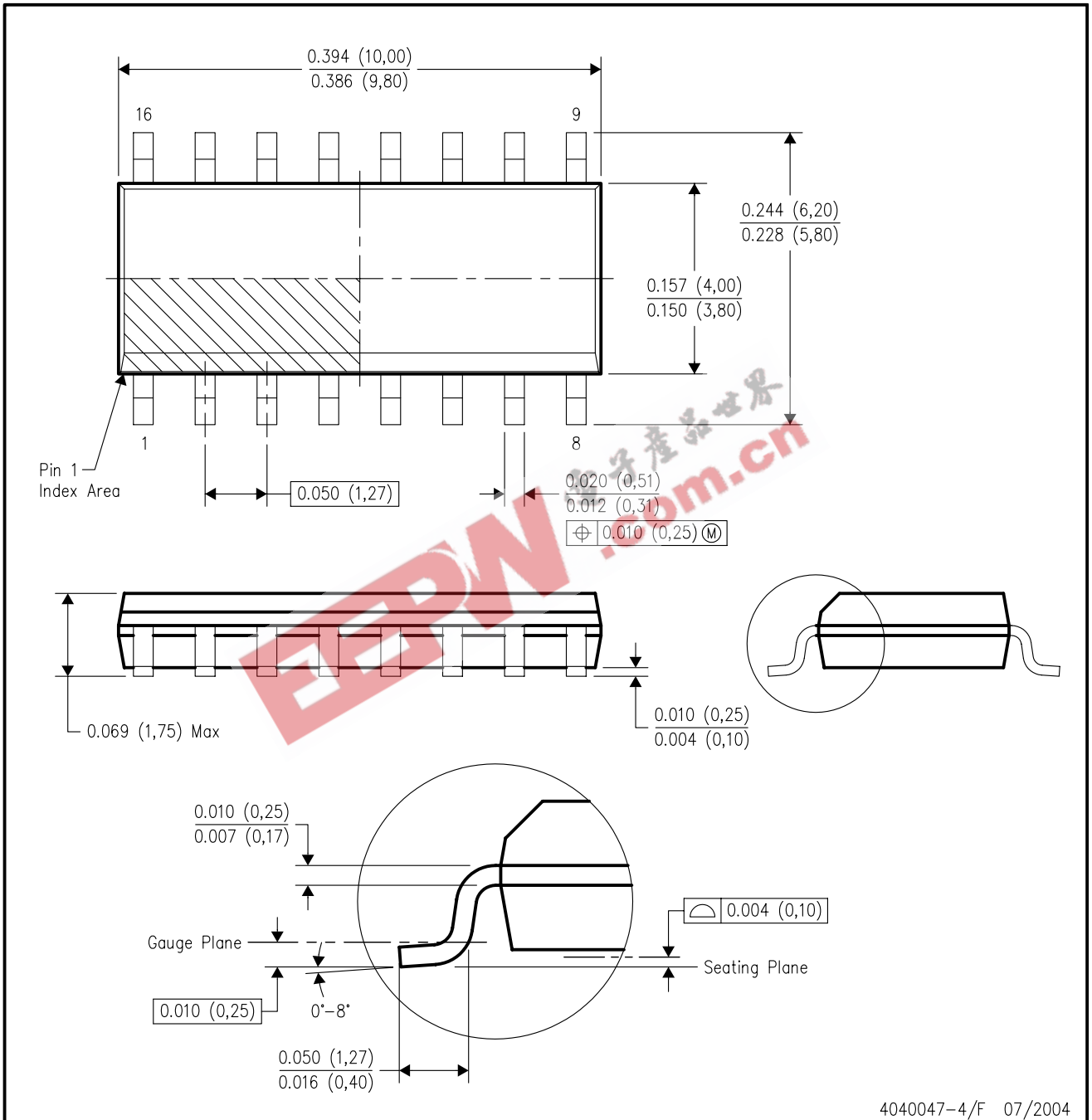


- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

MECHANICAL DATA

D (R-PDSO-G16)

PLASTIC SMALL-OUTLINE PACKAGE



4040047-4/F 07/2004

- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
 - D. Falls within JEDEC MS-012 variation AC.

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